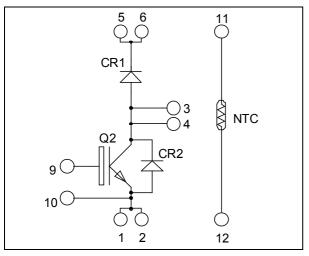
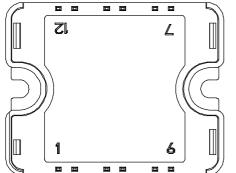


# Boost chopper Trench + Field Stop IGBT3 Power Module





Pins 1/2; 3/4; 5/6 must be shorted together

### Absolute maximum ratings

#### Symbol Parameter Max ratings Unit Collector - Emitter Breakdown Voltage 1700 V<sub>CES</sub> V $T_C = 25^{\circ}C$ 45 Continuous Collector Current $I_C$ $T_C = 80^{\circ}C$ 30 Α Pulsed Collector Current $T_C = 25^{\circ}C$ 70 I<sub>CM</sub> Gate - Emitter Voltage V V<sub>GE</sub> $\pm 20$ $T_C = 25^{\circ}C$ W $P_{D}$ Maximum Power Dissipation 210 RBSOA Reverse Bias Safe Operating Area $T_i = 125^{\circ}C$ 60A@1600V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

# $V_{CES} = 1700V$ $I_{C} = 30A$ @ $Tc = 80^{\circ}C$

#### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
    - Low tail current
    - Switching frequency up to 20 kHz
    - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

APTGT30DA170T1G-Rev 1 October, 2012



# All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

| Electrical Characteristics |                                      |   |                        |     |     |     |      |  |
|----------------------------|--------------------------------------|---|------------------------|-----|-----|-----|------|--|
| Symbol                     | Characteristic                       | Test Conditions                           |                        | Min | Тур | Max | Unit |  |
| I <sub>CES</sub>           | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 1700V$             |                        |     |     | 250 | μΑ   |  |
| V <sub>CE(sat)</sub>       | Collector Emitter saturation Voltage |   | $T_j = 25^{\circ}C$    |     | 2.0 | 2.4 | V    |  |
| V CE(sat)                  | Concetor Enniter saturation voltage  | $I_C = 30A$                               | $T_{j} = 125^{\circ}C$ |     | 2.4 |     | v    |  |
| V <sub>GE(th)</sub>        | Gate Threshold Voltage               | $V_{GE} = V_{CE}$ , $I_C = 1.5 \text{mA}$ |                        | 5.2 | 5.8 | 6.4 | V    |  |
| I <sub>GES</sub>           | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$               |                        |     |     | 600 | nA   |  |

# **Dynamic Characteristics**

| Symbol              | Characteristic               | Test Conditions  |                      | Min | Тур  | Max | Unit |
|---------------------|------------------------------|--|----------------------|-----|------|-----|------|
| Cies                | Input Capacitance            | $V_{GE} = 0V, V_{CE} = 25V$                                      |                      |     | 2500 |     | pF   |
| Cres                | Reverse Transfer Capacitance | f = 1 MHz  |                      |     | 90   |     | pr   |
| T <sub>d(on)</sub>  | Turn-on Delay Time           | Inductive Switch   | ing (25°C)           |     | 100  |     |      |
| T <sub>r</sub>      | Rise Time                    | $V_{GE} = \pm 15V$   |                      |     | 70   |     |      |
| T <sub>d(off)</sub> | Turn-off Delay Time          | $V_{Bus} = 900V$ $I_{C} = 30A$                                   |                      |     | 650  |     | ns   |
| $T_{\mathrm{f}}$    | Fall Time                    | $R_G = 18\Omega$   |                      | 80  |      |     |      |
| T <sub>d(on)</sub>  | Turn-on Delay Time           | Inductive Switch   |                      | 100 |      |     |      |
| Tr                  | Rise Time                    | $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 30A$ $R_G = 18\Omega$ |                      |     | 70   |     |      |
| T <sub>d(off)</sub> | Turn-off Delay Time          |  |                      |     | 750  |     | ns   |
| T <sub>f</sub>      | Fall Time                    |  |                      |     | 100  |     |      |
| Eon                 | Turn-on Switching Energy     | $V_{GE} = \pm 15V$ $V_{Bus} = 900V$                              | $T_j = 125^{\circ}C$ |     | 17   |     | mJ   |
| E <sub>off</sub>    | Turn-off Switching Energy    | $I_C = 30A$<br>$R_G = 18\Omega$                                  | $T_j = 125^{\circ}C$ |     | 15   |     | mJ   |

### Chopper diode ratings and characteristics

| Symbol           | Characteristic                          | Test Conditions                       |  | Min  | Тур | Max        | Unit |
|------------------|---|---------------------------------------|--|------|-----|------------|------|
| V <sub>RRM</sub> | Maximum Peak Repetitive Reverse Voltage |                                       |  | 1700 |     |            | V    |
| I <sub>RM</sub>  | Maximum Reverse Leakage Current         | V <sub>R</sub> =1700V                 | $T_i = 25^{\circ}C$ $T_i = 125^{\circ}C$ |      |     | 250<br>500 | μA   |
| I <sub>F</sub>   | DC Forward Current                      |                                       | $T_{\rm C} = 80^{\circ}{\rm C}$          |      | 50  | 200        | А    |
| $V_{\rm F}$      | Diode Forward Voltage                   | $I_{\rm F} = 50 A$ $V_{\rm GE} = 0 V$ | $T_j = 25^{\circ}C$                      |      | 1.8 | 2.2        | V    |
| • F              | Diode Forward Voltage                   |                                       | $T_{i} = 125^{\circ}C$                   |      | 1.9 |            | v    |
| +                | Deverse Deservery Time                  |                                       | $T_j = 25^{\circ}C$                      |      | 385 |            | na   |
| t <sub>rr</sub>  | Reverse Recovery Time                   |                                       | $T_{j} = 125^{\circ}C$                   |      | 490 |            | ns   |
| 0                |   | $I_F = 50A$                           | $T_j = 25^{\circ}C$                      |      | 14  |            | 0    |
| Q <sub>rr</sub>  | Reverse Recovery Charge                 | $V_{\rm R} = 900V$<br>di/dt =800A/µs  | $T_j = 125^{\circ}C$                     |      | 23  |            | μC   |
| Б                | Reverse Recovery Energy                 |                                       | $T_j = 25^{\circ}C$                      |      | 6   |            | mI   |
| Er               |   |                                       | $T_{j} = 125^{\circ}C$                   |      | 12  |            | mJ   |



### Thermal and package characteristics

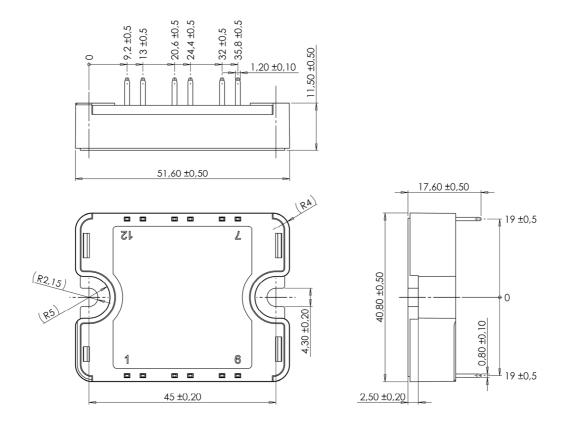
| Symbol            | Characteristic  |             |       | Min  | Тур | Max  | Unit |
|-------------------|---|-------------|-------|------|-----|------|------|
| $R_{thJC}$        | Junction to Case Thermal Resistance                           |             | IGBT  |      |     | 0.60 | °C/W |
|                   |   |             | Diode |      |     | 0.70 | C/ W |
| V <sub>ISOL</sub> | RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz |             |       | 4000 |     |      | V    |
| T <sub>J</sub>    | Operating junction temperature range                          |             |       | -40  |     | 150  |      |
| T <sub>STG</sub>  | Storage Temperature Range                                     |             |       | -40  |     | 125  | °C   |
| T <sub>C</sub>    | Operating Case Temperature                                    | -40         |       | 100  |     |      |      |
| Torque            | Mounting torque   | To heatsink | x M4  | 2    |     | 3    | N.m  |
| Wt                | Package Weight  |             |       |      | 80  | g    |      |

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol          | Characteristic              | Min | Тур  | Max | Unit |
|-----------------|-----------------------------|-----|------|-----|------|
| R <sub>25</sub> | Resistance @ 25°C           |     | 50   |     | kΩ   |
| B 25/85         | $T_{25} = 298.15 \text{ K}$ |     | 3952 |     | Κ    |

$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

### SP1 Package outline (dimensions in mm)

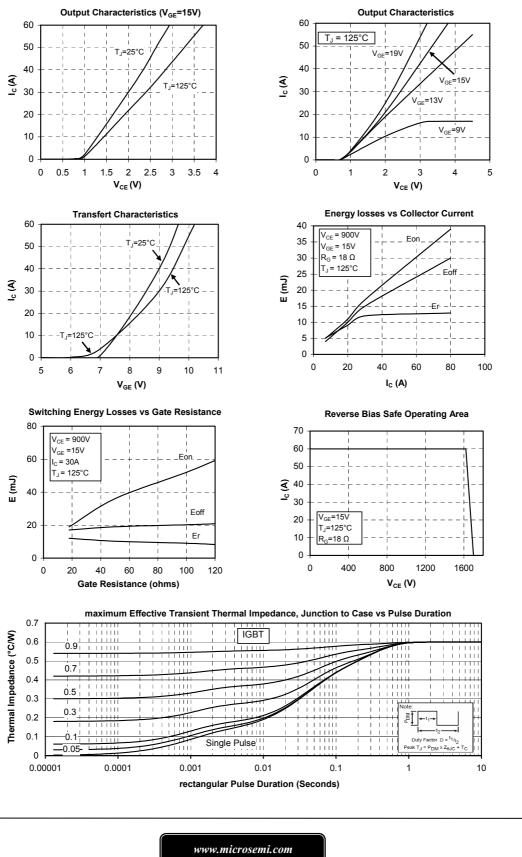


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

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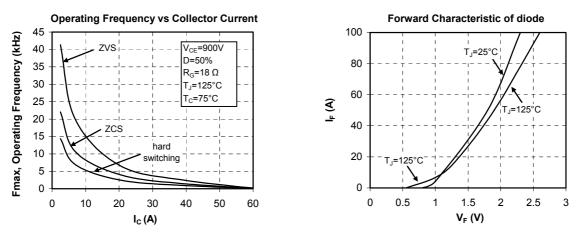
#### **Typical Performance Curve**

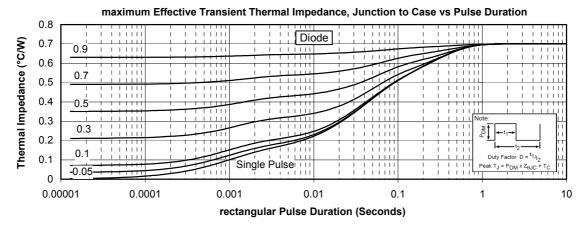


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